

## ABSTRACT

An electrostatic discharge (ESD) protection device having high holding current for latch-up immunity. The ESD protection circuit is formed in a semiconductor integrated circuit (IC) having protected circuitry. The ESD protection device includes a silicon controlled rectifier (SCR) coupled between a protected supply line of the IC and ground. A trigger device is coupled from the supply line to a first gate of the SCR, and a first substrate resistor is coupled between the first gate and ground. A first shunt resistor is coupled between the first gate and ground, wherein the shunt resistor has a resistance value lower than the substrate resistor.